

Please type a plus sign (+) inside this box →

O I P E
JCB
DEC 28 2004

Substitute for form 1449A/B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/811,979
				Filing Date	March 30, 2004
				First Named Inventor	KAMIYAMA et al.
				Group Art Unit	Unassigned
				Examiner Name	Unassigned
(Use as many sheets as necessary)				Attorney Docket Number	403018
Sheet	1	of	1		

U.S. PATENT DOCUMENTS

Examiner Signature

Long Pham

Date Considered

8/31/05

- A concise statement of relevance is being submitted in lieu of a translation. 37 CFR 1.98(a)(3).
 - An English-language equivalent/patent, or an English-language abstract, or an English-language version of the search report or action by a foreign patent office in a counterpart foreign application indicating the degree of relevance found by the foreign office is being submitted in lieu of a concise explanation of relevance under 37 CFR 1.98(a)(3).

Please type a plus sign (+) inside this box →

Substitute for form 1449A/B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/811,979
(Use as many sheets as necessary)				Filing Date	March 30, 2004
				First Named Inventor	KAMIYAMA
				Group Art Unit	2811
				Examiner Name	Unassigned
Sheet	1	of	1	Attorney Docket Number	403018

O I P E
J U L Y 1 6 2004
P A T E N T & T R A D E M A R K O F F I C E

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Doc. No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number (s), publisher, city and/or country where published.	Translation	
			Yes	No*†
HP	B 3	VAINONEN-AHLGREN, E. et al.: "Atomic layer deposition of hafnium and zirconium silicate thin films", <i>Computational Materials Science</i> , Vol. 27, No. 1-2, pp. 65-69, (March 2003).		
HP	B 4	HU, H. et al.; "MIM Capacitors Using Atomic-Layer-Deposited High-K (HfO_2) _{1-x} (Al_2O_5) _x Dielectrics", <i>IEEE Electron Device Letters</i> , Vol. 24, No. 2, pp. 60-62, (Feb. 2003).		

Examiner Signature

Long Pham

Date Considered

8/31/05

- A concise statement of relevance is being submitted in lieu of a translation. 37 CFR 1.98(a)(3).
 - An English-language equivalent/patent, or an English-language abstract, or an English-language version of the search report or action by a foreign patent office in a counterpart foreign application indicating the degree of relevance found by the foreign office is being submitted in lieu of a concise explanation of relevance under 37 CFR 1.98(a)(3).

Please type a plus sign (+) inside this box →

Substitute for form 1449A/B/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	Unassigned
				Filing Date	March 30, 2004
				First Named Inventor	Satoshi KAMIYAMA
				Group Art Unit	Unassigned
				Examiner Name	Unassigned
(Use as many sheets as necessary)				Attorney Docket Number	403018
Sheet	1	of	1		

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

Examiner Signature

bony pharynx

Date Considered

8/3/05

- A concise statement of relevance is being submitted in lieu of a translation. 37 CFR 1.98(a)(3).
 - + An English-language equivalent/patent, or an English-language abstract, or an English-language version of the search report or action by a foreign patent office in a counterpart foreign application indicating the degree of relevance found by the foreign office is being submitted in lieu of a concise explanation of relevance under 37 CFR 1.98(a)(3).